



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re: U.S. Patent Application 10 001,429) PATENT
German Title: Schreib-Leseverstärker für eine DRAM-)
Speicherzelle sowie DRAM-Speicher)
English Translation: Read/write amplifier for a DRAM)
Memory cell, and DRAM memory)
Applicant: Infineon Technologies, AG)
Inventors: Alexander Frey)
Attorney Docket No: 32226.14)

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

RECEIVED
APR 15 2002

Technology Center 2600
35 U.S.C. 133

Sir:

PRELIMINARY AMENDMENT

In the above-entitled patent application, please amend the application as follows:

In the Claims

1. (amended) A read/write amplifier for a DRAM memory cell, which, for evaluation of the information content of at least one DRAM memory cell, is connected or can be connected to at least one bit line and to at least one reference bit line, which in each case form a bit line pair, having a number of components for assessment, amplification and forwarding of voltage signals read from the bit lines and reference bit lines, in which case the read/write amplifier has a first read/write amplifier element and a second read/write amplifier element separate therefrom, and in that the individual amplifier components are divided between the two read/write amplifier elements.